MOSFETs Silicon N-channel MOS (U-MOSIV)

# **TPCP8011**

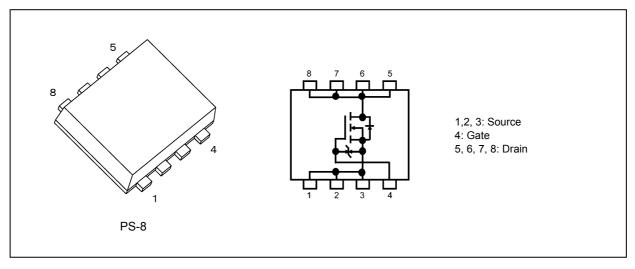
#### 1. Applications

- Motor Drivers
- Mobile Equipment

#### 2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Small gate charge :  $Q_{SW} = 4.7 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 25.5 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 40 \ V)$
- (6) Enhancement mode:  $V_{th} = 2$  to 3 V ( $V_{DS} = 10$  V,  $I_D = 1$  mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	40	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	5	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	20	
Power dissipation	(t = 5 s)	(Note 2)	PD	1.96	W
Power dissipation	(t = 5 s)	(Note 3)	PD	0.94	W
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	33.2	mJ
Avalanche current			I <sub>AR</sub>	5	Α
Channel temperature		(Note 5)	T <sub>ch</sub>	175	°C
Storage temperature		(Note 5)	T <sub>stg</sub>	-55 to 175	7

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics				Max	Unit
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R <sub>th(ch-a)</sub>	76.5	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)	R <sub>th(ch-a)</sub>	159.5	°C/W

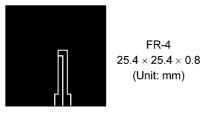
Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V<sub>DD</sub> = 25 V, T<sub>ch</sub> = 25°C (initial), L = 1.379 mH, R<sub>G</sub> = 1  $\Omega$ , I<sub>AR</sub> = 5 A

Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.



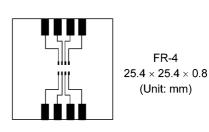
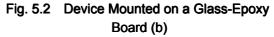


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

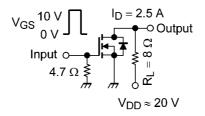
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±16 V, $V_{DS}$ = 0 V	_	_	±10	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	40	_	_	V
Drain-source breakdown voltage	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	20	—	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2	2.5	3	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 6 V, I <sub>D</sub> = 2.5 A	_	32	51.2	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A		25.5	31.8	

#### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		505	_	pF
Reverse transfer capacitance	C <sub>rss</sub>			66	_	
Output capacitance	C <sub>oss</sub>			115	_	
Switching time (rise time)	tr	See Figure 6.2.1	_	5.37	_	ns
Switching time (turn-on time)	t <sub>on</sub>	]		12	_	
Switching time (fall time)	t <sub>f</sub>	]		4.34	_	
Switching time (turn-off time)	t <sub>off</sub>	]	_	17.4	_	



Duty  $\leq$  1%, t<sub>w</sub> = 10  $\mu$ s

Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

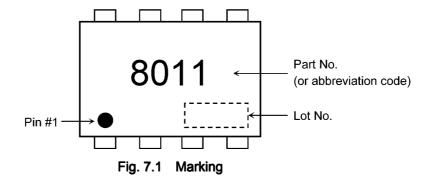
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 32 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 5 \text{ A}$	—	11.8	—	nC
Gate-source charge 1	Q <sub>gs1</sub>			2.1	_	
Gate-drain charge	Q <sub>gd</sub>		_	3.9	_	
Gate switch charge	Q <sub>SW</sub>		_	4.7	_	

#### 6.4. Source-Drain Characteristics (Ta = 25°C unless otherwise specified)

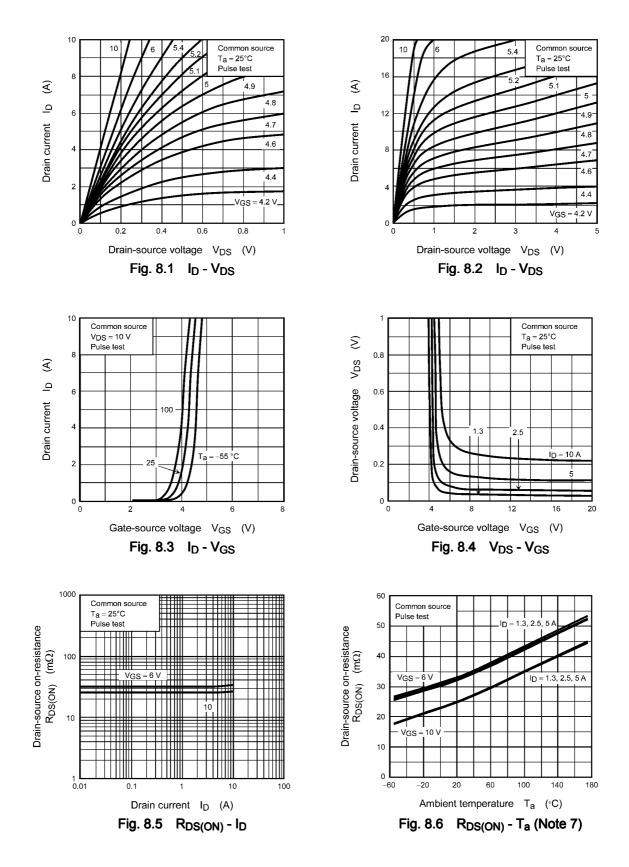
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 6)	I <sub>DRP</sub>	—	_	—	20	А
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V			-1.2	V

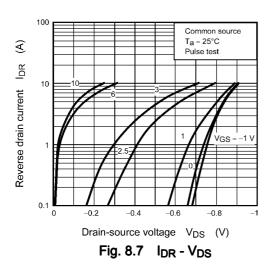
Note 6: Ensure that the channel temperature does not exceed 175°C.

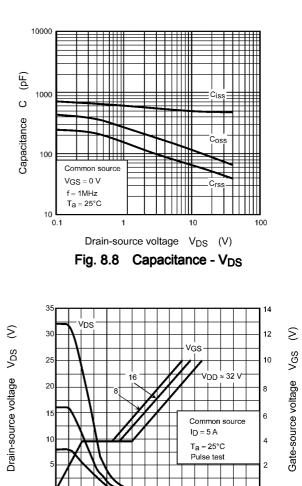
7. Marking

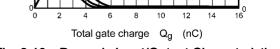


### 8. Characteristics Curves (Note)





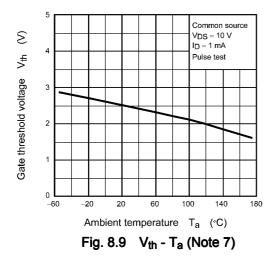


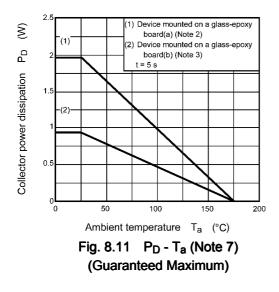


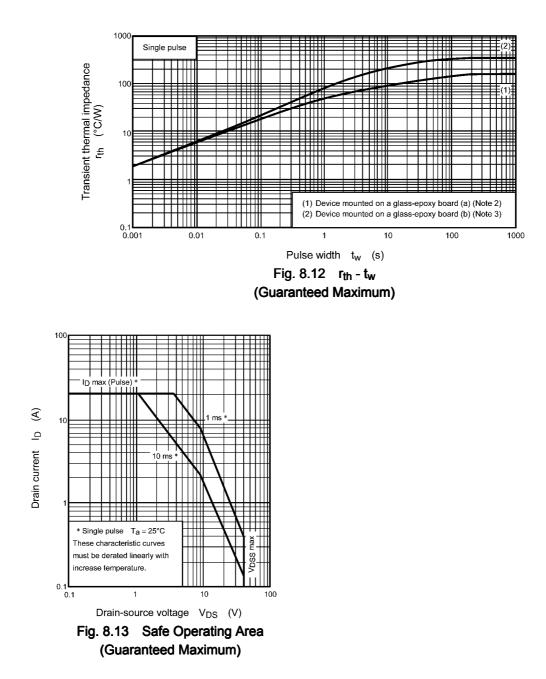
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10 12 14

Fig. 8.10 Dynamic Input/Output Characteristics



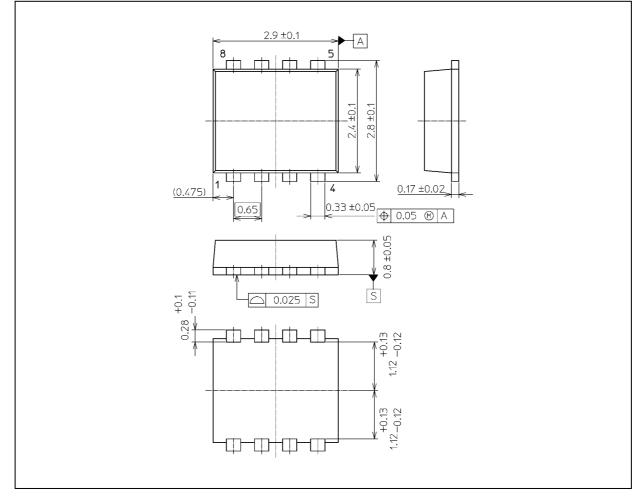




- Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.
- Note 7: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

#### Package Dimensions

Unit: mm



Weight: 0.017 g (typ.)

Package Name(s)

TOSHIBA: 2-3V1S

Nickname: PS-8

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